

SURFACE MOUNT HIGH DENSITY 1 AMP SILICON SCHOTTKY BRIDGE RECTIFIER MB120S

FEATURES

- Low forward voltage (0.76V TYP @ 1.0A)
- Low leakage current (0.2 μ A TYP @ 200V)
- High current rating: 1.0A
- High voltage rating: 200V

APPLICATIONS:

- Input rectification for LED lighting
- Power over Ethernet (PoE) peripherals
- General purpose full wave rectification

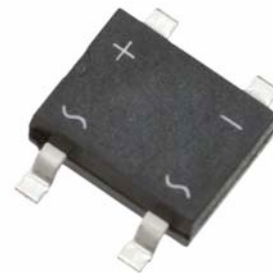
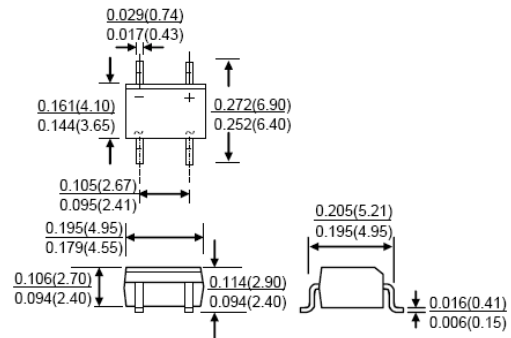
MECHANICAL DATA

Case: MBS

Epoxy: UL94V-O rate flame retardant

Lead: Lead Formed for Surface Mount

MBS (TO-269AA)



Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter	Symbol	MB120S	Unit
Maximum repetitive peak reverse voltage	VRRM	200	V
Working peak reverse voltage	VRWM	140	V
Maximum DC blocking voltage	VDC	200	V
Maximum average forward rectified current	IF(AV)	1	A
Peak forward surge current	IFSM	30	A
8.3ms single half sine-wave superimposed on rated load (JEDEC Method)			
Operating junction temperature range	TJ	-55 to +150	°C
Storage temperature range	TSTG	-55 to +150	°C

Electrical characteristics (Tc=25°C unless otherwise noted)

Parameter	Symbol	TYP	Max	Unit
Maximum instantaneous at IF=1A, Tj=25°C	VF	0.75	0.90	V
Maximum reverse current at working peak reverse voltage Tj=125°C	IR	0.2	50	μ A
		-	20	m'A

Thermal characteristics (Tc=25°C unless otherwise noted)

Parameter	Symbol	Unit
Typical thermal resistance	R0JA	85
	Rthjl	28
		°C/W

(1) Pulse test: 300 μ s pulse width, 1 % duty cycle

(2) Pulse test: Pulse width \leq 40 ms